

Saurav Roy

List of Publications by Year in descending order

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8
papers

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#	ARTICLE	IF	CITATIONS
1	High-k Oxide Field-Plated Vertical (001) In^{2+} -Ga ₂ O ₃ Schottky Barrier Diode With Baliga's Figure of Merit Over 1 GW/cm ² . IEEE Electron Device Letters, 2021, 42, 1140-1143.	3.9	86
2	Low temperature homoepitaxy of (010) In^{2+} -Ga ₂ O ₃ by metalorganic vapor phase epitaxy: Expanding the growth window. Applied Physics Letters, 2020, 117, .	3.3	56
3	Multi-kV Class In^{2+} -Ga ₂ O ₃ MESFETs With a Lateral Figure of Merit Up to 355 MW/cm ² . IEEE Electron Device Letters, 2021, 42, 1272-1275.	3.9	50
4	Schottky Barrier Height Engineering in In^{2+} -Ga ₂ O ₃ Using SiO ₂ Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	2.1	32
5	Design of a In^{2+} -Ga ₂ O ₃ Schottky Barrier Diode With p-Type III-Nitride Guard Ring for Enhanced Breakdown. IEEE Transactions on Electron Devices, 2020, 67, 4842-4848.	3.0	21
6	Delta-doped In^{2+} -Ga ₂ O ₃ films with narrow FWHM grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2020, 117, .	3.3	17
7	In Situ Dielectric Al ₂ O ₃ / In^{2+} -Ga ₂ O ₃ Interfaces Grown Using Metal-Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	5.1	17
8	2-D Analytical Modeling of Surface Potential and Threshold Voltage for Vertical Super-Thin Body FET. IEEE Transactions on Electron Devices, 2017, 64, 2106-2112.	3.0	11